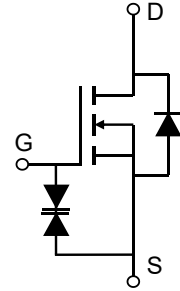


Description

Features

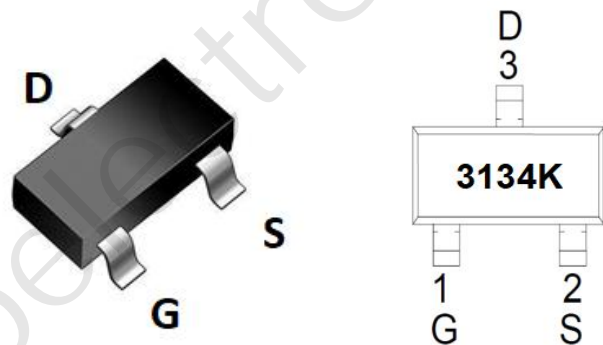
- 20V, 1A
 $R_{DS(ON)}$ Typ = 131mΩ @ $V_{GS} = 4.5V$
 $R_{DS(ON)}$ Typ = 190mΩ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- ESD Protected: 2KV



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMLTU3134K	3134K	SOT-23	TAPING	7"	3000	120000

Absolute Maximum Ratings (@ $T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	±10	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	1
		$T_A = 100^\circ C$	0.6
I_{DM}	Pulsed Drain Current ⁽¹⁾	4	A
P_D	Power Dissipation	$T_A = 25^\circ C$	0.26
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	490	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 10\text{V}$	-	-	± 10	μA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.4	0.65	1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 4.5\text{V}, I_D = 0.5\text{A}$	-	131	170	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 0.3\text{A}$	-	190	247	$\text{m}\Omega$

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 10\text{V},$ $f = 1\text{MHz}$	-	53	-	pF
C_{oss}	Output Capacitance		-	14	-	pF
C_{rss}	Reverse Transfer Capacitance		-	10	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 4.5\text{V}$ $V_{DS} = 10\text{V}, I_D = 0.9\text{A}$	-	1	-	nC
Q_{gs}	Gate Source Charge		-	0.28	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	0.22	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 4.5\text{V}, V_{DD} = 10\text{V}$ $I_D = 0.5\text{A}, R_{GEN} = 10\Omega$	-	2	-	ns
t_r	Turn-On Rise Time		-	19	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	10	-	ns
t_f	Turn-Off Fall Time		-	23	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}, I_S = 0.5\text{A}$	-	-	1	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	4	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Output Characteristics

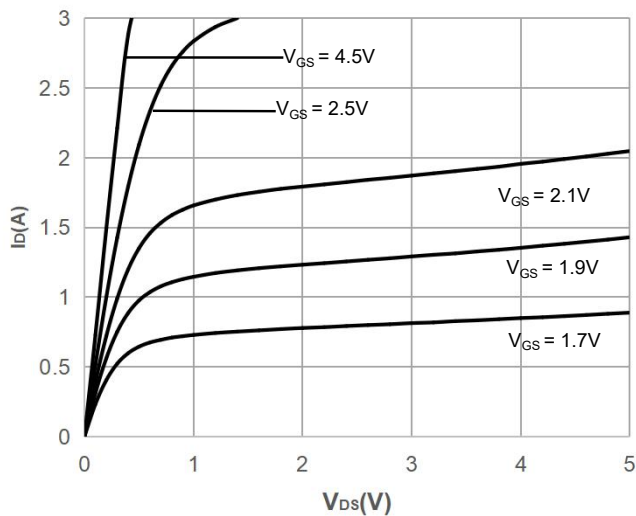


Figure 2: Typical Transfer Characteristics

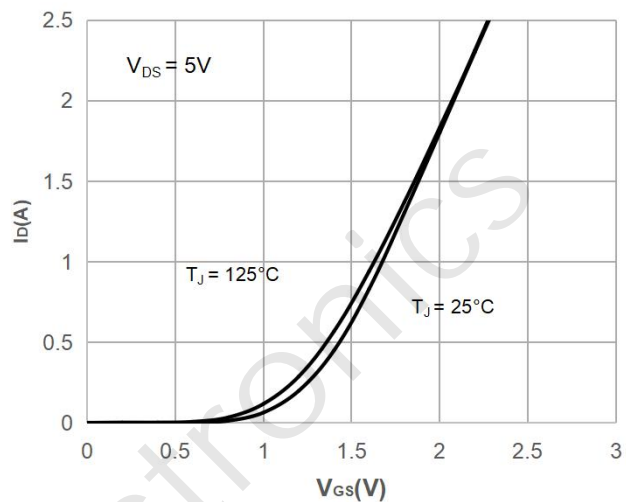


Figure 3: On-resistance vs. Drain Current

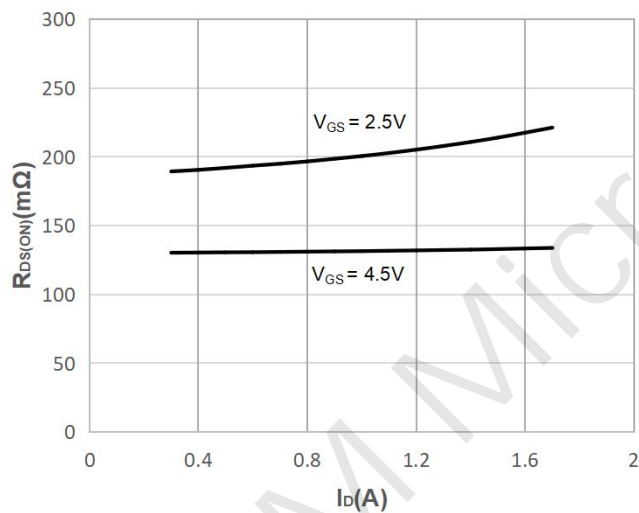


Figure 4: Body Diode Characteristics

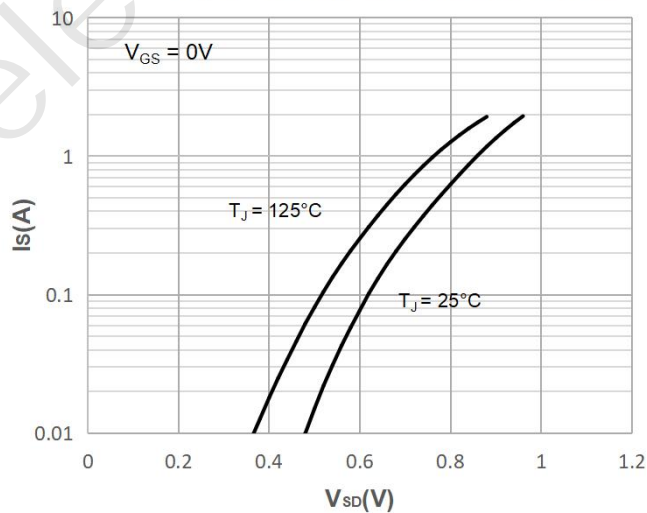


Figure 5: Gate Charge Characteristics

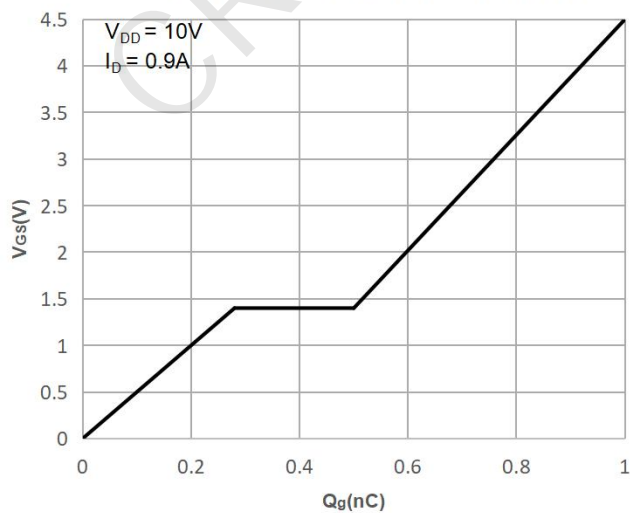
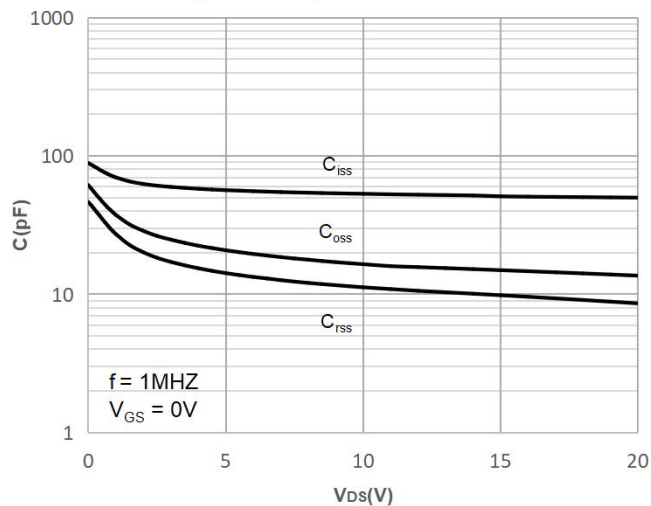


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

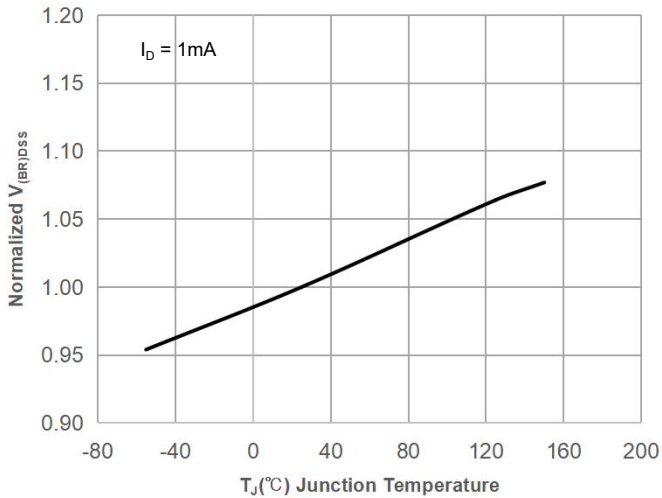


Figure 8: Normalized on Resistance vs. Junction Temperature

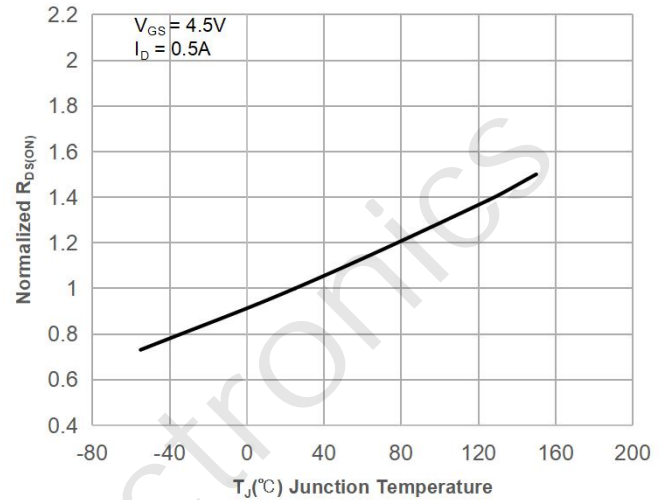


Figure 9: Maximum Safe Operating Area

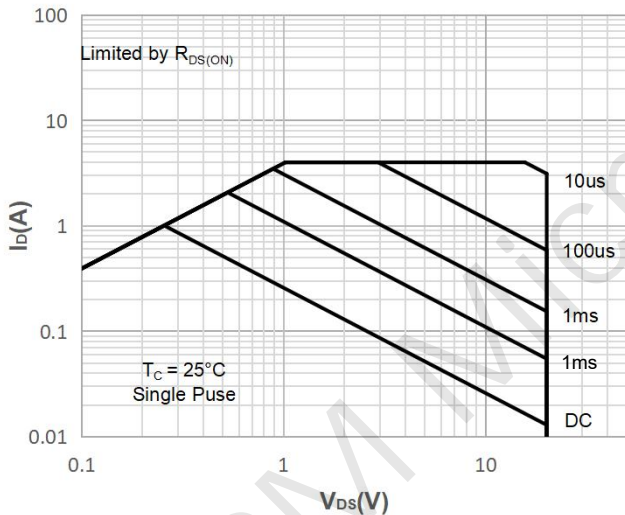


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

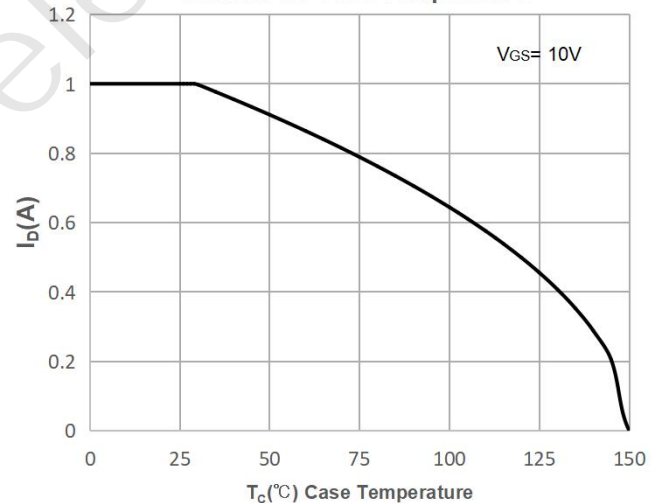


Figure 11: Normalized Maximum Transient Thermal Impedance

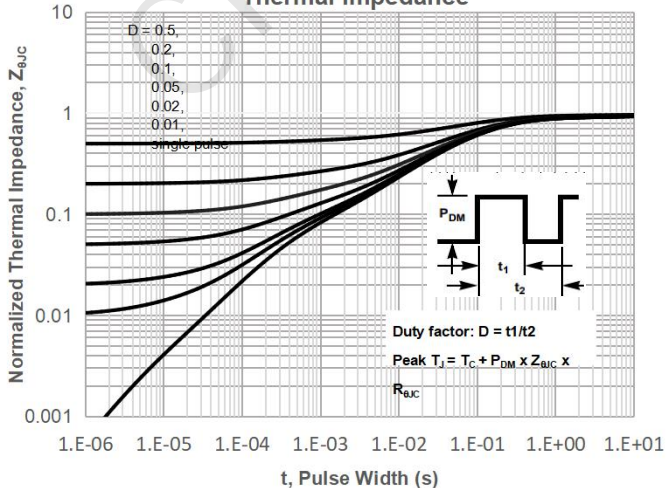
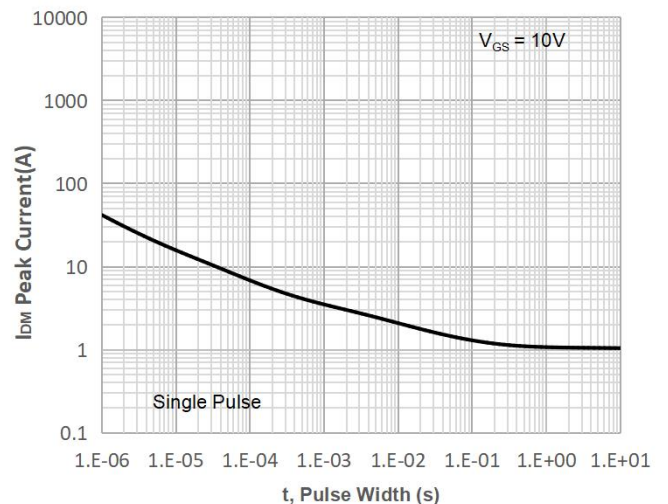


Figure 12: Peak Current Capacity



Test Circuit

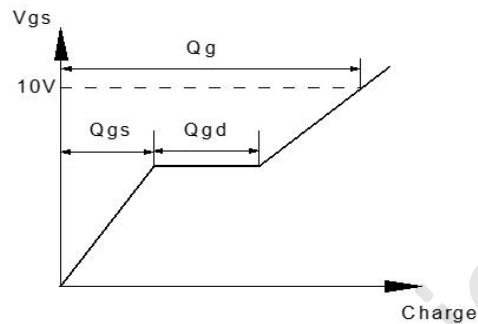
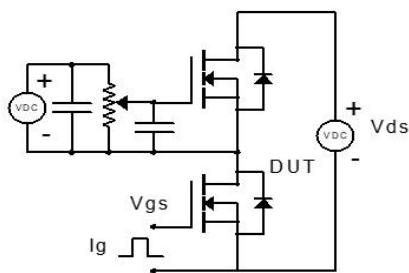


Figure 1: Gate Charge Test Circuit & Waveform

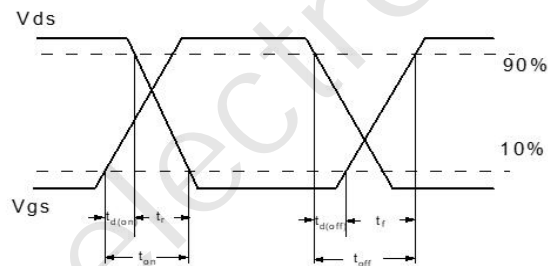
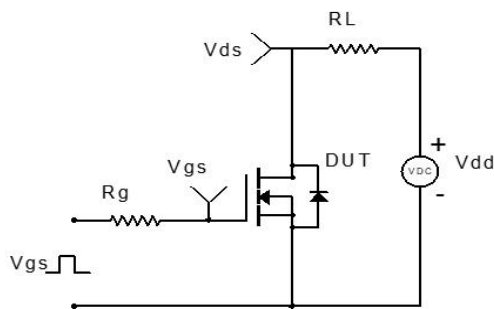


Figure 2: Resistive Switching Test Circuit & Waveform

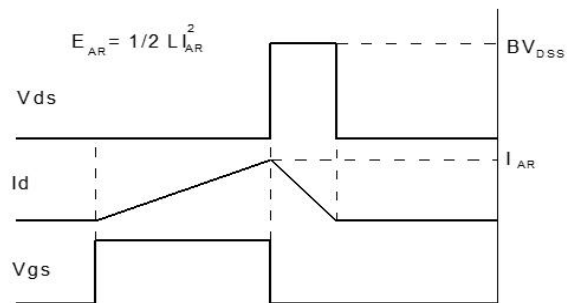
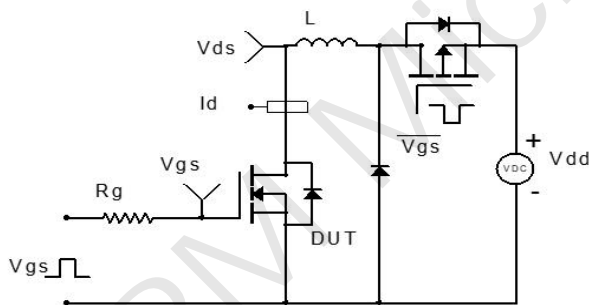


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

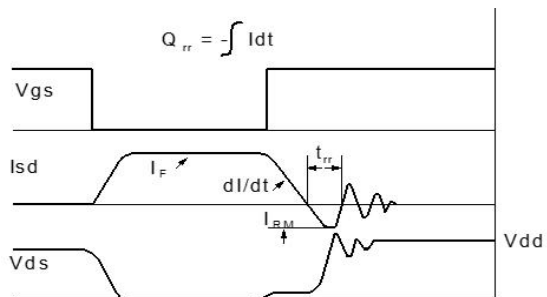
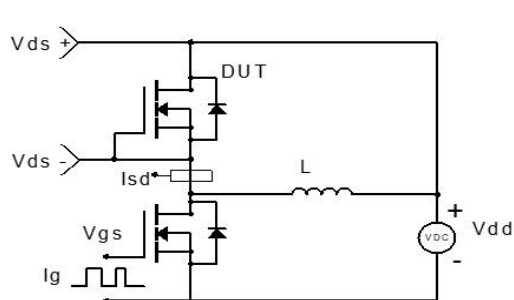
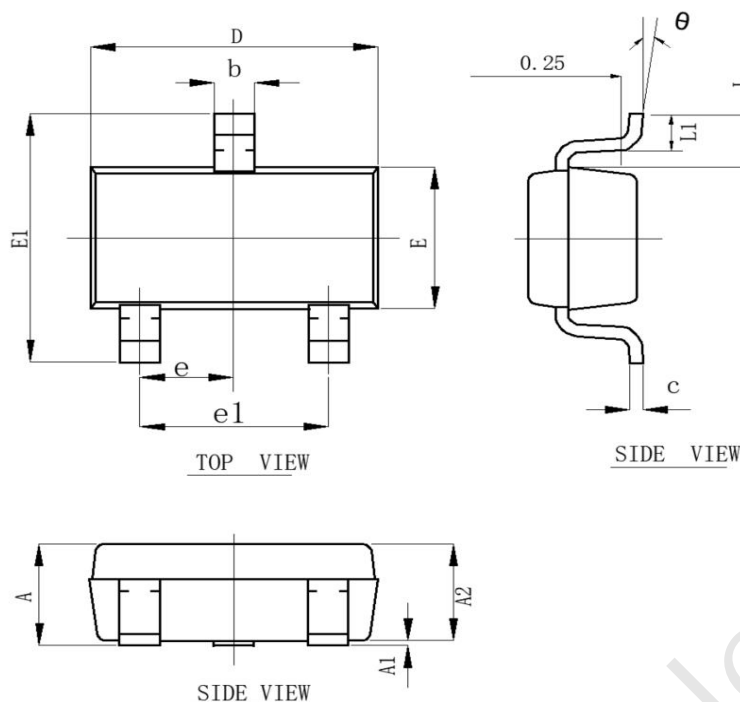


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23)




COMMON DIMENSIONS In Millimeters		
SYMBOL	MIN	MAX
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
L	0.550	REF.
θ	0°	8°
L1	0.300	0.500
e	0.950	TYP.
e1	1.800	2.000

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